Intel - EP1C4F400C6 Datasheet





Welcome to <u>E-XFL.COM</u>

Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	400
Number of Logic Elements/Cells	4000
Total RAM Bits	78336
Number of I/O	301
Number of Gates	-
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	400-BGA
Supplier Device Package	400-FBGA (21x21)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep1c4f400c6

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 1–1. Cyclone Device Features (Part 2 of 2)									
Feature	EP1C3	EP1C4	EP1C6	EP1C12	EP1C20				
Total RAM bits	59,904	78,336	92,160	239,616	294,912				
PLLs	1	2	2	2	2				
Maximum user I/O pins (1)	104	301	185	249	301				

Note to Table 1–1:

(1) This parameter includes global clock pins.

Cyclone devices are available in quad flat pack (QFP) and space-saving FineLine[®] BGA packages (see Tables 1–2 through 1–3).

Table 1–2. Cyclone Package Options and I/O Pin Counts										
Device	100-Pin TQFP (1)	144-Pin TQFP (1), (2)	240-Pin PQFP (1)	256-Pin FineLine BGA	324-Pin FineLine BGA	400-Pin FineLine BGA				
EP1C3	65	104	—	—	—	—				
EP1C4	—	—	—	—	249	301				
EP1C6	—	98	185	185	—	—				
EP1C12	—	—	173	185	249	—				
EP1C20	—	—	—	—	233	301				

Notes to Table 1–2:

(1) TQFP: thin quad flat pack.

PQFP: plastic quad flat pack.

(2) Cyclone devices support vertical migration within the same package (i.e., designers can migrate between the EP1C3 device in the 144-pin TQFP package and the EP1C6 device in the same package).

Vertical migration means you can migrate a design from one device to another that has the same dedicated pins, JTAG pins, and power pins, and are subsets or supersets for a given package across device densities. The largest density in any package has the highest number of power pins; you must use the layout for the largest planned density in a package to provide the necessary power pins for migration.

For I/O pin migration across densities, cross-reference the available I/O pins using the device pin-outs for all planned densities of a given package type to identify which I/O pins can be migrated. The Quartus[®] II software can automatically cross-reference and place all pins for you when given a device migration list. If one device has power or ground pins, but these same pins are user I/O on a different device that is in the migration path,the Quartus II software ensures the pins are not used as user I/O in the Quartus II software. Ensure that these pins are connected

performance and flexibility. Each LE can drive 30 other LEs through fast local and direct link interconnects. Figure 2–3 shows the direct link connection.



Figure 2–3. Direct Link Connection

LAB Control Signals

Each LAB contains dedicated logic for driving control signals to its LEs. The control signals include two clocks, two clock enables, two asynchronous clears, synchronous clear, asynchronous preset/load, synchronous load, and add/subtract control signals. This gives a maximum of 10 control signals at a time. Although synchronous load and clear signals are generally used when implementing counters, they can also be used with other functions.

Each LAB can use two clocks and two clock enable signals. Each LAB's clock and clock enable signals are linked. For example, any LE in a particular LAB using the labclk1 signal will also use labclkena1. If the LAB uses both the rising and falling edges of a clock, it also uses both LAB-wide clock signals. Deasserting the clock enable signal will turn off the LAB-wide clock.

Each LAB can use two asynchronous clear signals and an asynchronous load/preset signal. The asynchronous load acts as a preset when the asynchronous load data input is tied high.



Figure 2–11. C4 Interconnect Connections Note (1)

Note to Figure 2–11:

(1) Each C4 interconnect can drive either up or down four rows.

register outputs (number of taps $n \times \text{width } w$) must be less than the maximum data width of the M4K RAM block (×36). To create larger shift registers, multiple memory blocks are cascaded together.

Data is written into each address location at the falling edge of the clock and read from the address at the rising edge of the clock. The shift register mode logic automatically controls the positive and negative edge clocking to shift the data in one clock cycle. Figure 2–14 shows the M4K memory block in the shift register mode.

 w × m × n Shift Register

 m-Bit Shift Register

 w

 m-Bit Shift Register

Figure 2–14. Shift Register Memory Configuration

Memory Configuration Sizes

The memory address depths and output widths can be configured as $4,096 \times 1, 2,048 \times 2, 1,024 \times 4, 512 \times 8$ (or 512×9 bits), 256×16 (or 256×18 bits), and 128×32 (or 128×36 bits). The 128×32 - or 36-bit configuration

Table 2–7. Global Clock Network Sources (Part 2 of 2)									
Sou	rce	GCLKO	GCLK1	GCLK2	GCLK3	GCLK4	GCLK5	GCLK6	GCLK7
Dual-Purpose	DPCLK0 (3)	—	—	—	~	—	—	—	—
CIOCK PINS	DPCLK1 (3)	_	_	~	_	_	_	_	_
	DPCLK2	\checkmark	_	_	_	_	_	_	_
	DPCLK3	_	_	_	_	\checkmark	_		_
	DPCLK4	_	_	_	_	_	_	~	_
	DPCLK5 (3)	_	_	_	_	_	_	_	\checkmark
	DPCLK6	_	—	—	—	—	\checkmark	_	_
	DPCLK7	_	\checkmark	—	—	—		_	—

Notes to Table 2–7:

(1) EP1C3 devices only have one PLL (PLL 1).

(2) EP1C3 devices in the 100-pin TQFP package do not have dedicated clock pins CLK1 and CLK3.

(3) EP1C3 devices in the 100-pin TQFP package do not have the DPCLK0, DPCLK1, or DPCLK5 pins.

Clock Multiplication and Division

Cyclone PLLs provide clock synthesis for PLL output ports using $m/(n \times \text{post}$ scale counter) scaling factors. The input clock is divided by a pre-scale divider, n, and is then multiplied by the m feedback factor. The control loop drives the VCO to match $f_{\text{IN}} \times (m/n)$. Each output port has a unique post-scale counter to divide down the high-frequency VCO. For multiple PLL outputs with different frequencies, the VCO is set to the least-common multiple of the output frequencies that meets its frequency specifications. Then, the post-scale dividers scale down the output frequencies required from one PLL are 33 and 66 MHz, the VCO is set to 330 MHz (the least-common multiple in the VCO's range).

Each PLL has one pre-scale divider, *n*, that can range in value from 1 to 32. Each PLL also has one multiply divider, *m*, that can range in value from 2 to 32. Global clock outputs have two post scale G dividers for global clock outputs, and external clock outputs have an E divider for external clock output, both ranging from 1 to 32. The Quartus II software automatically chooses the appropriate scaling factors according to the input frequency, multiplication, and division values entered.

Table 2–10. DQ Pin Groups (Part 2 of 2)								
Device	Package	Number of × 8 DQ Pin Groups	Total DQ Pin Count					
EP1C6	144-pin TQFP	4	32					
	240-pin PQFP	4	32					
	256-pin FineLine BGA	4	32					
EP1C12	240-pin PQFP	4	32					
	256-pin FineLine BGA	4	32					
	324-pin FineLine BGA	8	64					
EP1C20	324-pin FineLine BGA	8	64					
	400-pin FineLine BGA	8	64					

Note to Table 2–10:

A programmable delay chain on each DQS pin allows for either a 90° phase shift (for DDR SDRAM), or a 72° phase shift (for FCRAM) which automatically center-aligns input DQS synchronization signals within the data window of their corresponding DQ data signals. The phase-shifted DQS signals drive the global clock network. This global DQS signal clocks DQ signals on internal LE registers.

These DQS delay elements combine with the PLL's clocking and phase shift ability to provide a complete hardware solution for interfacing to high-speed memory.

The clock phase shift allows the PLL to clock the DQ output enable and output paths. The designer should use the following guidelines to meet 133 MHz performance for DDR SDRAM and FCRAM interfaces:

- The DQS signal must be in the middle of the DQ group it clocks
- Resynchronize the incoming data to the logic array clock using successive LE registers or FIFO buffers
- LE registers must be placed in the LAB adjacent to the DQ I/O pin column it is fed by

Figure 2–34 illustrates DDR SDRAM and FCRAM interfacing from the I/O through the dedicated circuitry to the logic array.

⁽¹⁾ EP1C3 devices in the 100-pin TQFP package do not have any DQ pin groups in I/O bank 1.

Figure 2–34. DDR SDRAM and FCRAM Interfacing



Programmable Drive Strength

The output buffer for each Cyclone device I/O pin has a programmable drive strength control for certain I/O standards. The LVTTL and LVCMOS standards have several levels of drive strength that the designer can control. SSTL-3 class I and II, and SSTL-2 class I and II support a minimum setting, the lowest drive strength that guarantees the I_{OH}/I_{OL}

of the standard. Using minimum settings provides signal slew rate control to reduce system noise and signal overshoot. Table 2–11 shows the possible settings for the I/O standards with drive strength control.

Table 2–11. Programmable Drive Strength Note (1)					
I/O Standard	I _{OH} /I _{OL} Current Strength Setting (mA)				
LVTTL (3.3 V)	4				
VTTL (3.3 V) VCMOS (3.3 V) VTTL (2.5 V)	8				
	12				
	16				
	24(2)				
LVCMOS (3.3 V)	2				
	4				
	8				
	12(2)				
LVTTL (2.5 V)	2				
LVTTL (2.5 V)	8				
	12				
	16 <i>(2)</i>				
LVTTL (1.8 V)	2				
	8				
	12(2)				
LVCMOS (1.5 V)	2				
	4				
	8(2)				

Notes to Table 2–11:

- (1) SSTL-3 class I and II, SSTL-2 class I and II, and 3.3-V PCI I/O Standards do not support programmable drive strength.
- (2) This is the default current strength setting in the Quartus II software.

Open-Drain Output

Cyclone devices provide an optional open-drain (equivalent to an open-collector) output for each I/O pin. This open-drain output enables the device to provide system-level control signals (e.g., interrupt and write-enable signals) that can be asserted by any of several devices.

The Cyclone V_{CCINT} pins must always be connected to a 1.5-V power supply. If the V_{CCINT} level is 1.5 V, then input pins are 1.5-V, 1.8-V, 2.5-V, and 3.3-V tolerant. The V_{CCIO} pins can be connected to either a 1.5-V, 1.8-V, 2.5-V, or 3.3-V power supply, depending on the output requirements. The output levels are compatible with systems of the same voltage as the power supply (i.e., when V_{CCIO} pins are connected to a 1.5-V power supply, the output levels are compatible with 1.5-V systems). When V_{CCIO} pins are connected to a 3.3-V power supply, the output levels are compatible with 1.5-V systems). When V_{CCIO} pins are connected to a 3.3-V and is compatible with 3.3-V or 5.0-V systems. Table 2–14 summarizes Cyclone MultiVolt I/O support.

Table 2–14. Cyclone MultiVolt I/O Support Note (1)										
V (V)	Input Signal Output Signal									
VCCIO (V)	1.5 V	1.8 V	2.5 V	3.3 V	5.0 V	1.5 V	1.8 V	2.5 V	3.3 V	5.0 V
1.5	\checkmark	\checkmark	(2)	(2)	_	\checkmark	_	_	_	—
1.8	\checkmark	\checkmark	✓ (2)	(2)	_	🗸 (3)	\checkmark	_	_	_
2.5	-	_	~	~	_	🗸 (5)	 (5) 	\checkmark		—
3.3	_	_	✓ (4)	\checkmark	🗸 (6)	 (7) 	(7)	(7)	~	 (8)

Notes to Table 2–14:

(1) The PCI clamping diode must be disabled to drive an input with voltages higher than V_{CCIO}.

- (2) When V_{CCIO} = 1.5-V or 1.8-V and a 2.5-V or 3.3-V input signal feeds an input pin, higher pin leakage current is expected. Turn on Allow voltage overdrive for LVTTL / LVCMOS input pins in the Assignments > Device > Device and Pin Options > Pin Placement tab when a device has this I/O combinations.
- (3) When V_{CCIO} = 1.8-V, a Cyclone device can drive a 1.5-V device with 1.8-V tolerant inputs.
- (4) When V_{CCIO} = 3.3-V and a 2.5-V input signal feeds an input pin, the V_{CCIO} supply current will be slightly larger than expected.
- (5) When $V_{CCIO} = 2.5$ -V, a Cyclone device can drive a 1.5-V or 1.8-V device with 2.5-V tolerant inputs.
- (6) Cyclone devices can be 5.0-V tolerant with the use of an external resistor and the internal PCI clamp diode.
- (7) When V_{CCIO} = 3.3-V, a Cyclone device can drive a 1.5-V, 1.8-V, or 2.5-V device with 3.3-V tolerant inputs.
- (8) When V_{CCIO} = 3.3-V, a Cyclone device can drive a device with 5.0-V LVTTL inputs but not 5.0-V LVCMOS inputs.

Power Sequencing and Hot Socketing

Because Cyclone devices can be used in a mixed-voltage environment, they have been designed specifically to tolerate any possible power-up sequence. Therefore, the V_{CCIO} and V_{CCINT} power supplies may be powered in any order.

Signals can be driven into Cyclone devices before and during power up without damaging the device. In addition, Cyclone devices do not drive out during power up. Once operating conditions are reached and the device is configured, Cyclone devices operate as specified by the user.

Figure 3–1 shows the timing requirements for the JTAG signals.



Figure 3–1. Cyclone JTAG Waveforms

Table 3–4 shows the JTAG timing parameters and values for Cyclone devices.

Table 3-	Table 3–4. Cyclone JTAG Timing Parameters and Values									
Symbol	Parameter	Min	Max	Unit						
t _{JCP}	TCK clock period	100	_	ns						
t _{JCH}	TCK clock high time	50	_	ns						
t _{JCL}	TCK clock low time	50	_	ns						
t _{JPSU}	JTAG port setup time	20	_	ns						
t _{JPH}	JTAG port hold time	45	_	ns						
t _{JPCO}	JTAG port clock to output		25	ns						
t _{JPZX}	JTAG port high impedance to valid output		25	ns						
t _{JPXZ}	JTAG port valid output to high impedance	_	25	ns						
t _{JSSU}	Capture register setup time	20	_	ns						
t _{JSH}	Capture register hold time	45	_	ns						
t _{JSCO}	Update register clock to output	_	35	ns						
t _{JSZX}	Update register high impedance to valid output	_	35	ns						
t _{JSXZ}	Update register valid output to high impedance	—	35	ns						

Table 4–5. LVCMOS Specifications									
Symbol	Parameter	Conditions	Minimum	Maximum	Unit				
V _{CCIO}	Output supply voltage	—	3.0	3.6	V				
V _{IH}	High-level input voltage	—	1.7	4.1	V				
V _{IL}	Low-level input voltage	—	-0.5	0.7	V				
V _{OH}	High-level output voltage	V _{CCIO} = 3.0, I _{OH} = -0.1 mA	V _{CCIO} – 0.2	_	V				
V _{OL}	Low-level output voltage	$V_{CCIO} = 3.0,$ $I_{OL} = 0.1 \text{ mA}$	_	0.2	V				

Table 4–6. 2.5-V I/O Specifications									
Symbol	Parameter	Conditions	Minimum	Maximum	Unit				
V _{CCIO}	Output supply voltage	—	2.375	2.625	V				
V _{IH}	High-level input voltage	_	1.7	4.1	V				
V _{IL}	Low-level input voltage	—	-0.5	0.7	V				
V _{OH}	High-level output voltage	I _{OH} = -0.1 mA	2.1	_	V				
		I _{OH} = -1 mA	2.0	_	V				
		$I_{OH} = -2 \text{ to } -16 \text{ mA} (11)$	1.7	_	V				
V _{OL}	Low-level output voltage	I _{OL} = 0.1 mA	_	0.2	V				
		I _{OH} = 1 mA	_	0.4	V				
		I _{OH} = 2 to 16 mA <i>(11)</i>		0.7	V				

Table 4–7. 1.8-V I/O Specifications									
Symbol	Parameter	Conditions	Minimum	Maximum	Unit				
V _{CCIO}	Output supply voltage	—	1.65	1.95	V				
V _{IH}	High-level input voltage	_	$0.65 \times V_{CCIO}$	2.25 <i>(12)</i>	V				
V _{IL}	Low-level input voltage	_	-0.3	$0.35 \times V_{CCIO}$	V				
V _{OH}	High-level output voltage	$I_{OH} = -2$ to -8 mA (11)	$V_{\text{CCIO}} - 0.45$	_	V				
V _{OL}	Low-level output voltage	I _{OL} = 2 to 8 mA (11)	—	0.45	V				

Table 4–8. 1.5-V I/O Specifications									
Symbol	Parameter	Conditions	Minimum	Maximum	Unit				
V _{CCIO}	Output supply voltage	—	1.4	1.6	V				
V _{IH}	High-level input voltage	-	$0.65 \times V_{CCIO}$	V _{CCIO} + 0.3 (12)	V				
V _{IL}	Low-level input voltage	-	-0.3	$0.35 \times V_{CCIO}$	V				
V _{OH}	High-level output voltage	I _{OH} = -2 mA (11)	$0.75 \times V_{CCIO}$	_	V				
V _{OL}	Low-level output voltage	I _{OL} = 2 mA (11)	_	$\begin{array}{c} 0.25 \times \\ V_{\text{CCIO}} \end{array}$	V				

Table 4–9. 2.5-V LVDS I/O SpecificationsNote (13)										
Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit				
V _{CCIO}	I/O supply voltage	—	2.375	2.5	2.625	V				
V _{OD}	Differential output voltage	$R_L = 100 \Omega$	250	_	550	mV				
ΔV_{OD}	Change in V _{OD} between high and low	R _L = 100 Ω	_	_	50	mV				
V _{OS}	Output offset voltage	$R_L = 100 \ \Omega$	1.125	1.25	1.375	V				
ΔV_{OS}	Change in V _{OS} between high and low	R _L = 100 Ω	_	_	50	mV				
V _{TH}	Differential input threshold	V _{CM} = 1.2 V	-100	_	100	mV				
V _{IN}	Receiver input voltage range	_	0.0	—	2.4	V				
RL	Receiver differential input resistor	_	90	100	110	Ω				

Table 4–10. 3.3-V PCI Specifications (Part 1 of 2)										
Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit				
V _{CCIO}	Output supply voltage	—	3.0	3.3	3.6	V				
V _{IH}	High-level input voltage	_	$0.5 \times V_{CCIO}$	_	V _{CCIO} + 0.5	V				
V _{IL}	Low-level input voltage	_	-0.5	_	$0.3 \times V_{CCIO}$	V				

Table 4–22. IOE Internal Timing Microparameter Descriptions							
Symbol	Parameter						
t _{SU}	IOE input and output register setup time before clock						
t _H	IOE input and output register hold time after clock						
t _{CO}	IOE input and output register clock-to-output delay						
t _{PIN2COMBOUT_R}	Row input pin to IOE combinatorial output						
t _{PIN2COMBOUT_C}	Column input pin to IOE combinatorial output						
t _{COMBIN2PIN_R}	Row IOE data input to combinatorial output pin						
t _{COMBIN2PIN_C}	Column IOE data input to combinatorial output pin						
t _{CLR}	Minimum clear pulse width						
t _{PRE}	Minimum preset pulse width						
t _{CLKHL}	Minimum clock high or low time						

Table 4–23. M4	Table 4–23. M4K Block Internal Timing Microparameter Descriptions							
Symbol	Parameter							
t _{M4KRC}	Synchronous read cycle time							
t _{M4KWC}	Synchronous write cycle time							
t _{M4KWERESU}	Write or read enable setup time before clock							
t _{M4KWEREH}	Write or read enable hold time after clock							
t _{M4KBESU}	Byte enable setup time before clock							
t _{M4KBEH}	Byte enable hold time after clock							
t _{M4KDATAASU}	A port data setup time before clock							
t _{M4KDATAAH}	A port data hold time after clock							
t _{M4KADDRASU}	A port address setup time before clock							
t _{M4KADDRAH}	A port address hold time after clock							
t _{M4KDATABSU}	B port data setup time before clock							
t _{M4KDATABH}	B port data hold time after clock							
t _{M4KADDRBSU}	B port address setup time before clock							
t _{M4KADDRBH}	B port address hold time after clock							
t _{M4KDATACO1}	Clock-to-output delay when using output registers							
t _{M4KDATACO2}	Clock-to-output delay without output registers							
t _{M4KCLKHL}	Minimum clock high or low time							
t _{M4KCLR}	Minimum clear pulse width							

Table 4–34. EP1C6 Column Pin Global Clock External I/O Timing Parameters											
Symbol	-6 Spee	d Grade	-7 Spee	d Grade	-8 Spee	Unit					
	Min	Max	Min	Max	Min	Max	UIIII				
t _{INSU}	2.691	—	3.094	_	3.496		ns				
t _{INH}	0.000	_	0.000		0.000	_	ns				
t _{outco}	2.000	3.917	2.000	4.503	2.000	5.093	ns				
t _{INSUPLL}	1.513	_	1.739	_	1.964	_	ns				
t _{INHPLL}	0.000	—	0.000	_	0.000	_	ns				
toutcopll	0.500	2.038	0.500	2.343	0.500	2.651	ns				

Tables 4–34 through 4–35 show the external timing parameters on column and row pins for EP1C6 devices.

Table 4–35. EP1C6 Row Pin Global Clock External I/O Timing Parameters										
Symbol	-6 Spee	d Grade	-7 Spee	d Grade	-8 Spee	l lmit				
	Min	Max	Min	Max	Min	Max	UIII			
t _{INSU}	2.774	—	3.190	_	3.605	—	ns			
t _{INH}	0.000	_	0.000	—	0.000	—	ns			
t _{outco}	2.000	3.817	2.000	4.388	2.000	4.963	ns			
t _{INSUPLL}	1.596	_	1.835	—	2.073	—	ns			
t _{INHPLL}	0.000		0.000		0.000		ns			
toutcopll	0.500	1.938	0.500	2.228	0.500	2.521	ns			

Tables 4–36 through 4–37 show the external timing parameters on column and row pins for EP1C12 devices.

Table 4–36. EP1C12 Column Pin Global Clock External I/O Timing Parameters (Part 1 of 2)										
Symbol	-6 Spee	d Grade	-7 Speed Grade -8 Speed Grade				Unit			
	Min	Max	Min	Max	Min	Max	UIII			
t _{INSU}	2.510	_	2.885	_	3.259	—	ns			
t _{INH}	0.000	_	0.000	_	0.000	_	ns			
tO _{UTCO}	2.000	3.798	2.000	4.367	2.000	4.940	ns			
t _{INSUPLL}	1.588	_	1.824	_	2.061	_	ns			

Table 4–40. Cyclone I/O Standard Column Pin Input Delay Adders (Part 2 of 2)									
I/O Standard	-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit		
	Min	Max	Min	Max	Min	Max	Unit		
SSTL-2 class II		-278	—	-320		-362	ps		
LVDS		-261	_	-301	_	-340	ps		

Table 4–41. Cyclone I/O Standard Row Pin Input Delay Adders									
1/0 Standard	-6 Speed Grade		-7 Speed Grade		-8 Spee	d Grade	Unit		
i/O Stanuaru	Min	Max	Min	Max	Min	Max	Unit		
LVCMOS	—	0	—	0	—	0	ps		
3.3-V LVTTL	—	0	—	0	—	0	ps		
2.5-V LVTTL	—	27	—	31	—	35	ps		
1.8-V LVTTL	—	182	—	209	—	236	ps		
1.5-V LVTTL	—	278	—	319	—	361	ps		
3.3-V PCI (1)	—	0	—	0	—	0	ps		
SSTL-3 class I	—	-250	—	-288	—	-325	ps		
SSTL-3 class II	—	-250	—	-288	—	-325	ps		
SSTL-2 class I	—	-278	—	-320	—	-362	ps		
SSTL-2 class II	—	-278	—	-320	—	-362	ps		
LVDS	_	-261		-301	_	-340	ps		

Table 4–42. Cyclone I/O Standard Output Delay Adders for Fast Slew Rate on Column Pins (Part 1 of 2)										
Standard		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit		
		Min	Max	Min	Max	Min	Min Max			
LVCMOS	2 mA	—	0	—	0	—	0	ps		
	4 mA	—	-489	—	-563	-	-636	ps		
	8 mA	—	-855	—	-984	-	-1,112	ps		
	12 mA	—	-993	—	-1,142		-1,291	ps		
3.3-V LVTTL	4 mA	—	0	—	0	-	0	ps		
	8 mA	—	-347	—	-400	-	-452	ps		
	12 mA	—	-858	—	-987	-	-1,116	ps		
	16 mA	—	-819	—	-942	—	-1,065	ps		
	24 mA	—	-993	—	-1,142	_	-1,291	ps		

Table 4–42. Cyclone I/O Standard Output Delay Adders for Fast Slew Rate on Column Pins (Part 2 of 2)										
Standard		-6 Spee	d Grade	-7 Spee	ed Grade	-8 Speed Grade		1114		
		Min	Max	Min	Max	Min	Max	Unit		
2.5-V LVTTL	2 mA	—	329		378	—	427	ps		
	8 mA	—	-661	—	-761	-	-860	ps		
	12 mA	—	-655	—	-754	_	-852	ps		
	16 mA	—	-795	—	-915	-	-1034	ps		
1.8-V LVTTL	2 mA	—	4	—	4	-	5	ps		
	8 mA	—	-208	—	-240	_	-271	ps		
	12 mA	—	-208	—	-240	_	-271	ps		
1.5-V LVTTL	2 mA	—	2,288	—	2,631	-	2,974	ps		
	4 mA	—	608	—	699	-	790	ps		
	8 mA	—	292	—	335	-	379	ps		
SSTL-3 class I		—	-410	—	-472	-	-533	ps		
SSTL-3 class I	1	—	-811	—	-933	_	-1,055	ps		
SSTL-2 class I		—	-485	—	-558	-	-631	ps		
SSTL-2 class I	1	_	-758	_	-872	_	-986	ps		
LVDS		_	-998	—	-1,148	_	-1,298	ps		

Table 4–43. Cyclone I/O Standard Output Delay Adders for Fast Slew Rate on Row Pins (Part 1 of 2)										
Observational		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit		
Stallu	aru	Min	Max	Min	Max M		Max	UIII		
LVCMOS	2 mA	—	0	—	0	—	0	ps		
	4 mA	—	-489	—	-563	-	-636	ps		
	8 mA	—	-855	—	-984	-	-1,112	ps		
	12 mA	—	-993	—	-1,142		-1,291	ps		
3.3-V LVTTL	4 mA	—	0	—	0	_	0	ps		
	8 mA	—	-347	—	-400	-	-452	ps		
	12 mA	—	-858	—	-987		-1,116	ps		
	16 mA	—	-819	—	-942	_	-1,065	ps		
	24 mA	—	-993	—	-1,142	-	-1,291	ps		
2.5-V LVTTL	2 mA	—	329	—	378		427	ps		
	8 mA	—	-661	—	-761	-	-860	ps		
	12 mA	—	-655	—	-754	_	-852	ps		
	16 mA	_	-795	_	-915	_	-1,034	ps		

Table 4–44. Cyclone I/O Standard Output Delay Adders for Slow Slew Rate on Column Pins (Part 2 of 2)								
L/O Standard		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
1/0 3141	lualu	Min	Max	Min	Max	Min Max		UIII
1.5-V LVTTL	2 mA	—	6,789	—	7,807	—	8,825	ps
	4 mA	—	5,109	—	5,875		6,641	ps
	8 mA	—	4,793	—	5,511		6,230	ps
SSTL-3 class I		—	1,390	_	1,598		1,807	ps
SSTL-3 class II		—	989	_	1,137		1,285	ps
SSTL-2 class I		—	1,965	_	2,259		2,554	ps
SSTL-2 class II		—	1,692	_	1,945		2,199	ps
LVDS		_	802	_	922	_	1,042	ps

Table 4–45. Cyclone I/O Standard Output Delay Adders for Slow Slew Rate on Row Pins (Part 1 of 2)								
I/O Standard		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		1114
		Min	Max	Min	Max	Min	Max	Unit
LVCMOS	2 mA	—	1,800	—	2,070	_	2,340	ps
	4 mA	—	1,311	—	1,507		1,704	ps
	8 mA	—	945	—	1,086	_	1,228	ps
	12 mA	—	807	—	928	-	1,049	ps
3.3-V LVTTL	4 mA	—	1,831	—	2,105	-	2,380	ps
	8 mA	—	1,484	—	1,705	-	1,928	ps
	12 mA	—	973	—	1,118	_	1,264	ps
	16 mA	—	1,012	—	1,163	_	1,315	ps
	24 mA	—	838	—	963	-	1,089	ps
2.5-V LVTTL	2 mA	—	2,747	—	3,158	_	3,570	ps
	8 mA	—	1,757	—	2,019	-	2,283	ps
	12 mA	—	1,763	—	2,026	-	2,291	ps
	16 mA	—	1,623	—	1,865	-	2,109	ps
1.8-V LVTTL	2 mA	—	5,506	—	6,331	-	7,157	ps
	8 mA	—	4,220	—	4,852	_	5,485	ps
	12 mA	—	4,008	—	4,608	-	5,209	ps
1.5-V LVTTL	2 mA	—	6,789	—	7,807	-	8,825	ps
	4 mA	_	5,109	_	5,875	_	6,641	ps
	8 mA	—	4,793	—	5,511	_	6,230	ps
3.3-V PCI			923	_	1,061		1,199	ps

July 2003 v1.1	Updated timing information. Timing finalized for EP1C6 and EP1C20 devices. Updated performance information. Added PLL Timing section.	_
May 2003 v1.0	Added document to Cyclone Device Handbook.	_



Figure 5–1. Cyclone Device Packaging Ordering Information

Referenced Documents

This chapter references the following documents:

- Package Information for Cyclone Devices chapter in the Cyclone Device Handbook
- Quartus II Handbook

Document Revision History

Table 5–1 shows the revision history for this chapter.

Table 5–1. Document Revision History					
Date and Document Version	Changes Made	Summary of Changes			
May 2008 v1.4	Minor textual and style changes. Added "Referenced Documents" section.	_			
January 2007 v1.3	Added document revision history.	_			
August 2005 v1.2	Minor updates.	_			